

<b>SANYO</b>	No.4318	<b>2SJ308</b>
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

### Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

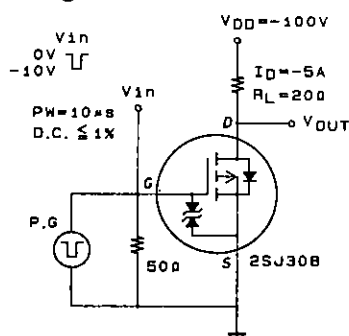
### Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Drain to Source Voltage	$V_{DS}$	-250	V
Gate to Source Voltage	$V_{GS}$	$\pm 30$	V
Drain Current(DC)	$I_D$	-9	A
Drain Current(Pulse)	$I_{DP}$	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	-36 A
Allowable Power Dissipation	$P_D$	2.0	W
		$T_c = 25^\circ\text{C}$	40 W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics at $T_a = 25^\circ\text{C}$

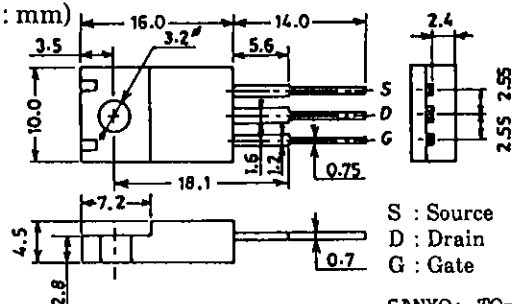
			min	typ	max	unit
D-S Breakdown Voltage	$V_{(BR)DS}$	$I_D = -1\text{mA}, V_{GS} = 0$	-250			V
G-S Breakdown Voltage	$V_{(BR)GS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	$\pm 30$			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -250\text{V}, V_{GS} = 0$			-100	$\mu A$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 25\text{V}, V_{DS} = 0$			$\pm 10$	$\mu A$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.5		-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}, I_D = -5\text{A}$	6	10		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -5\text{A}, V_{GS} = -10\text{V}$	0.35	0.48		$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		2700		pF
Output Capacitance	$C_{oss}$	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		500		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		225		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		40		ns
Rise Time	$t_r$	"		75		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		320		ns
Fall Time	$t_f$	"		260		ns
Diode Forward Voltage	$V_{SD}$	$I_S = -9\text{A}, V_{GS} = 0$	-1.0	-1.5		V

### Switching Time Test Circuit



### Package Dimensions 2063

(unit: mm)

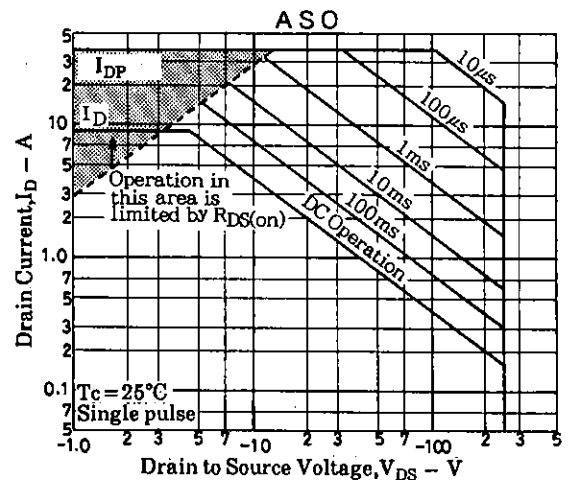
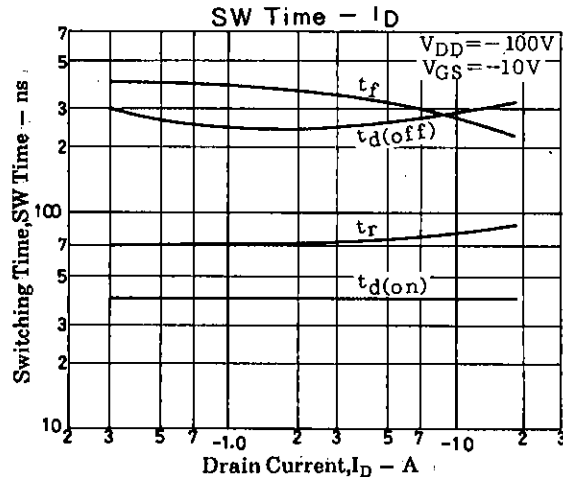
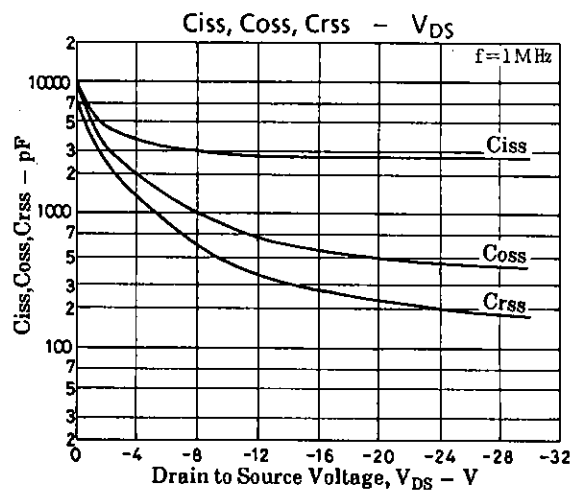
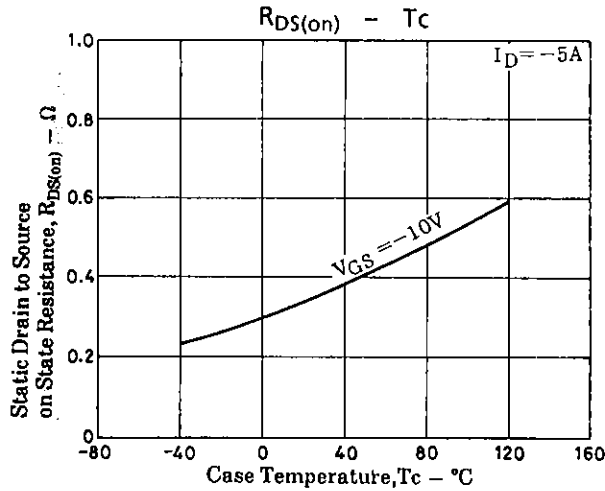
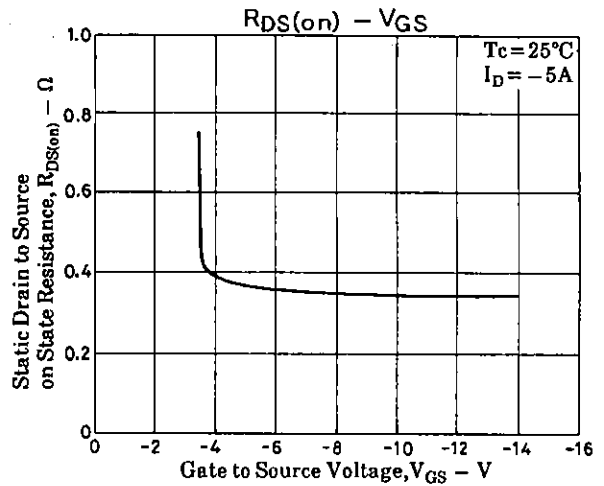
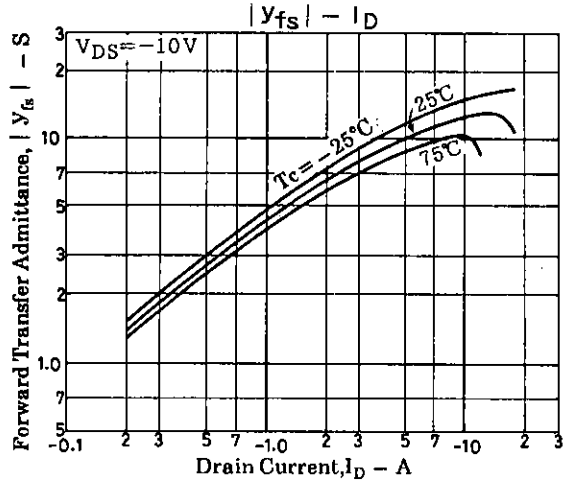
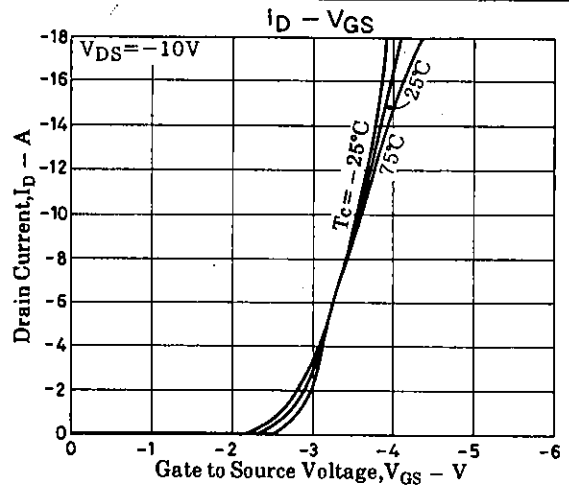
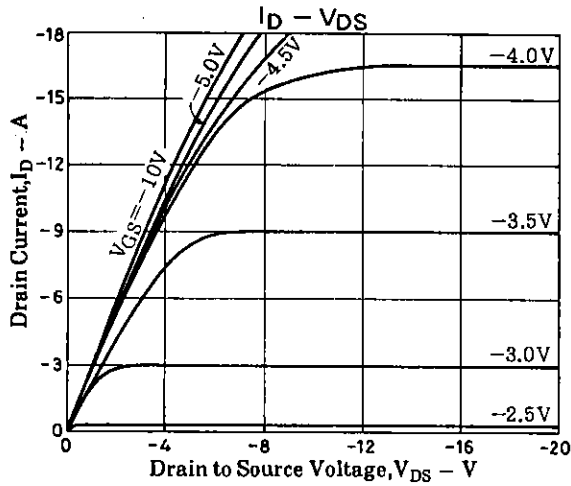


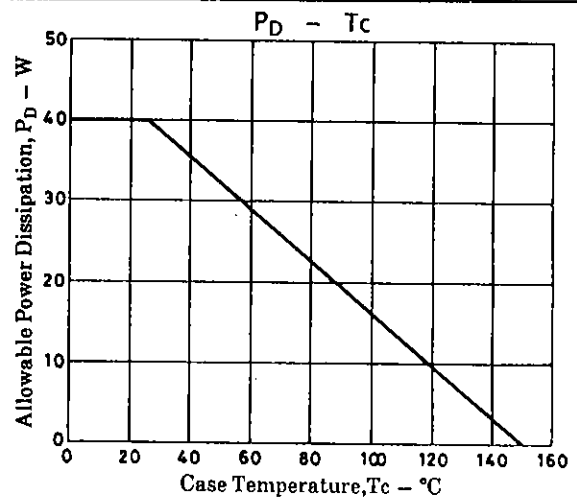
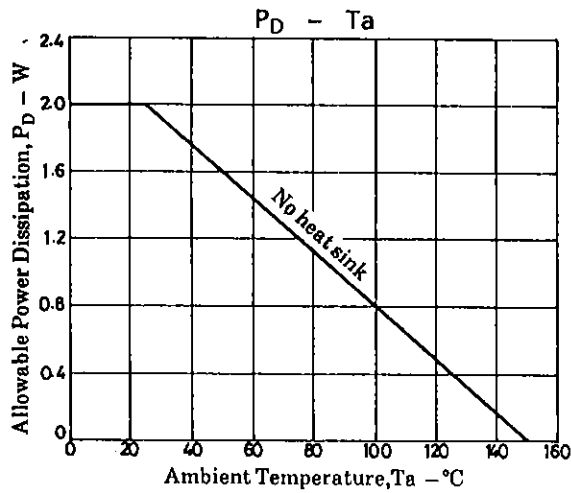
SANYO: TO-220ML

**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

53093TH (KOTO) AX-9095 No.4318-1/3





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